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03/07/02

Sc/690

U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10091461	03/07/2002	438		2812	
**APPLICANTS: Ito Masaaki;					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED: JAPAN 038745/2001 03/12/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>			RESCIND <input type="checkbox"/>		
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no			ATTORNEY DOCKET NO		
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no			00862.022541		
Verified and Acknowledged Examiner's initials					
TITLE : SOI substrate, annealing method therefor, semiconductor device having the SOI substrate, and method of manufacturing the same					
U.S. DPT. OF COM. / PAT. & TM. PTO-426L (Rev. 12-94)					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg.
		Print Fig.	
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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